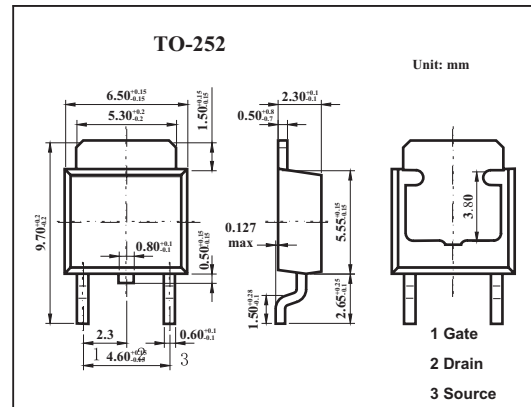


MOS Field Effect Transistor 2SK3507

■ Features

- 4.5 V drive available
- Low on-state resistance
 $R_{DS(on)1} = 45 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 11 \text{ A)}$
- Low gate charge
 $Q_G = 8.5 \text{ nC TYP. (} V_{DD} = 24 \text{ V, } V_{GS} = 10 \text{ V, } I_D = 22 \text{ A)}$
- Built-in G-S protection diode
- Surface mount package available



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	± 16	V
Drain current	I_D	± 22	A
	I_{DP}^*	± 45	A
Power dissipation	P_D	$T_c=25^\circ\text{C}$	20
		$T_A=25^\circ\text{C}$	1.5
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain cut-off current	I_{DSS}	$V_{DS}=30\text{V}, V_{GS}=0$			10	μA
Gate leakage current	I_{GSS}	$V_{GS} = \pm 16\text{V}, V_{DS}=0$			± 1	μA
Gate cutoff voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}, I_D=1\text{mA}$	1.5		2.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=4.0\text{V}, I_D=11\text{A}$	6			S
Drain to source on-state resistance	$R_{DS(on)1}$	$V_{GS}=10\text{V}, I_D=11\text{A}$		28	45	$\text{m}\Omega$
	$R_{DS(on)2}$	$V_{GS}=4.5\text{V}, I_D=11\text{A}$		46	76	$\text{m}\Omega$
Input capacitance	C_{iss}	$V_{DS}=10\text{V}, V_{GS}=0, f=1\text{MHz}$		360		pF
Output capacitance	C_{oss}		125		pF	
Reverse transfer capacitance	C_{rss}		65		pF	
Turn-on delay time	t_{on}		6.6		ns	
Rise time	t_r	$I_D=11\text{A}, V_{GS(on)}=10\text{V}, R_L=10\Omega, V_{DD}=15\text{V}$		3.6		ns
Turn-off delay time	t_{off}			16		ns
Fall time	t_f			5.3		ns
Total Gate Charge	Q_G				8.5	
Gate to Source Charge	Q_{GS}	$I_D=22\text{A}, V_{DD}=24\text{V}, V_{GS}=10\text{V}$		2		nC
Gate to Drain Charge	Q_{GD}			2.1		nC